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CIRCUIT CONNECTING MATERIAL, FILM-LIKE CIRCUIT CONNECTING MATERIAL USING THE SAME, CIRCUIT MEMBER CONNECTING STRUCTURE, AND METHOD OF PRODUCING THE SAME

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	Abstract of WO 2005	5002002 (A1)				
		es a circuit connecting material ch other a circuit member (30)			200	
		(32) and an insulation layer (33)	30		at the second	
		h other on the surface (31a) of	33e 31 31s 32 33			
a substrate (31), and a circuit member (40) having an electrode (42) and an insulation layer (43) formed						
adjacent each other on the surface (41a) of a						
	substrate (41), the ed	dges (33a, 43a) of the insulation	* } * } * } * }	72	<i>\$222</i>	
		thicker than the electrodes (32, rfaces (31a, 41a) used as	9230	200		10
		the circuit connecting material	THITTH.	111	1111	
contains an adhesive agent composition (51) and						
electrically conductive particles (12) whose mean						
		article size is from 1 mum to less than 10mum and hose hardness is 1.961 - 6.865 GPa, and when the				
	circuit connecting ma	ircuit connecting material undergoes hardening				
		elasticity modulus at 40 C is 0.5				
	 3 GPa and its mean at 25 C to 100 C is 3 	n thermal expansion coefficient				
	at 25 0 to 100 0 is 3	0 - 200 ppilir O.				

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